IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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ation of:) DIVISIONAL) PATENT APPLICATION	
Yanjun Ma, Douglas James Tweet, and David Russell Evans) September 11, 2003	
Unknown) Attorney Docket No. SLA0828 (SLA0514D)	
Herewith) Parent Application:	
INTEGRATED CIRCUIT METAL OXIDE SEMICONDUCTOR TRANSISTOR) Serial No. 10/072,248) Filed: February 7, 2002) Pending in Group Art) Unit 2814	
)) Examiner: Douglas A.) Wille	
	Anticipated Classification: Class: 257 Subclass: 288	
	Yanjun Ma, Douglas James Tweet, and David Russell Evans Unknown Herewith INTEGRATED CIRCUIT METAL OXIDE SEMICONDUCTOR	

CERTIFICATE OF MAILING BY "EXPRESS MAIL" UNDER 37 C.F.R. 1.10

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I hereby certify that this correspondence is being deposited With the United States Postal Service, utilizing the "Express Mail" Post Office to Addressee" service addressed to Mail Stop PATENT APPLICATION, Hon. Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, and mailed on the above Date of Mailing with the above "Express Mail" mailing label number.

Victoria Woods

Signature Date: September 11, 2003

DIVISIONAL APPLICATION UNDER 37 C.F.R. §1.53(b)

Mail Stop PATENT APPLICATION Hon. Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

The undersigned, attorney-of-record in parent application Serial No. 10/072,248, filed February 7, 2002, entitled "Silicon-Germanium MOSFET with Deposited Gate Dielectric and Metal Gate Electrode and Method for Making the Same," hereby requests the filing of a Divisional Application under the provisions of 37 C.F.R. §1.53(b).

Identification of the Parent of the Present Divisional Application:

Serial No.:

10/072,248

Filed:

February 7, 2002

Title:

Silicon-Germanium MOSFET with Deposited Gate

Dielectric and Metal Gate Electrode and Method for

Making the Same

Inventors:

Yanjun Ma, Douglas James Tweet, and David

Russell Evans

Status:

Pending

Copy of Present Divisional Application:

Enclosed is a copy of the present divisional application which incorporates the following changes from the as-filed specification and drawings in parent application Serial No. 10/072,248: The titled has been revised, an introductory cross-reference section has been added on page 1, and formal drawings have replaced the as-filed drawings. The present divisional application includes the following papers:

- X No. of Pages in Specification: 18 No. of Claims: 19
- X No. of Sheets of Drawings: 5 Formal: X or Informal:
- X Copy of the Declaration (signed by all inventors) in parent application Serial No. 10/072,248.

X Copy of the Power of Attorney in parent application Serial No. 10/072,248.

Parent application Serial No. 10/072,248, filed February 7, 2002, entitled "Silicon-Germanium MOSFET with Deposited Gate Dielectric and Metal Gate Electrode and Method for Making the Same" is hereby incorporated herein by reference.

Delete the Following Inventor(s) for This Application: None

Amendments:

X Please amend the enclosed specification as follows:

Cancel claims 8-19.

Filing Fee

The Divisional Patent Application filing fee is calculated as shown below after cancellation of claims 8 through 19:

·			Rate Small Entity/	
No.	1	No.	Other Than	_
Filed		Extra	Small Entity	r
Basic			\$375.00	
Fee			\$750.00	\$ 750.00
Total			\$ 9.00	
Claims _7_	(<u>20)</u>	= <u>0</u> X	\$18.00 =	\$ 36.00
Independent			\$42.00	
Claims 1	<u>(3)</u>	= <u>0</u> X	\$84.00 =	\$ 00.00
First Presentation			\$140.00	
Multiple Depend	lent Claim(s)_	0	\$280.00 =	\$ 00.00
	Total PAT	ENT APPLICAT	ION FILING FEE	\$ 750.00

^{*} If the difference is less than zero, enter "O".

^{**} Count claims after any amendment.

The total fee associated with this communication is as follows:

Patent application filing fee

\$ 750.00

TOTAL FEE DUE:

\$ 750.00

Method of Payment of Fees

- A check in the amount of the TOTAL FEE DUE is enclosed.
- <u>X</u> Please charge Deposit Account No. 19-1457 in the amount of \$\frac{\$786.00}{\$}\$. A duplicate copy of this authorization is enclosed.
- X The Commissioner is hereby authorized to charge underpayment of any fees associated with this communication, or credit any overpayment, to Deposit Account No. 19-1457. A duplicate copy of this authorization is enclosed.

Correspondence Address

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Respectfully submitted.

David C. Ripma Reg. No. 27,672

Date: 1/11/V)

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